# P-Channel 100-V (D-S) MOSFET

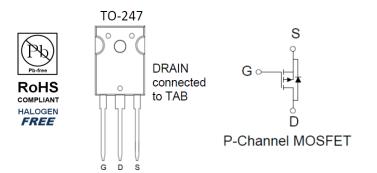
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- · Fast switching speed

### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	Id (A)		
-100	22 @ V <sub>GS</sub> = -10V	-90 <sup>a</sup>		
	25 @ V <sub>GS</sub> = -4.5V	-90		



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage	V <sub>DS</sub>	-100	V			
Gate-Source Voltage				V		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	-90	۸		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-360	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>S</sub>	-90	А		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	500	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	R <sub>θJA</sub>	40	°C/W			
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	0.29	C/W			

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA		
	L	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -10 V$	-110			А		
Droin Source On Registence a	r	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -45 \text{ A}$			22 mC			
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -40 \text{ A}$			25	mΩ		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -45 \text{ A}$		65		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -45 \text{ A}, V_{GS} = 0 \text{ V}$		-0.9		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = -4.5 V,		154		nC		
Gate-Source Charge	$Q_gs$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.3 \text{ V},$ $I_D = -20 \text{ A}$		50				
Gate-Drain Charge	$Q_gd$	1 <u>0</u> – 20 M		42				
Turn-On Delay Time	t <sub>d(on)</sub>			16		ns		
Rise Time	t <sub>r</sub>	$V_{DS} = -50 \text{ V}, \text{ R}_{L} = 2.5 \Omega,$ $I_{D} = -20 \text{ A},$		17				
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D = -20 \text{ A},$ $V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		432				
Fall Time	t <sub>f</sub>	$V_{\text{GEN}} = 10$ V, $V_{\text{GEN}} = 0.22$		129				
Input Capacitance	C <sub>iss</sub>			6717				
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = -50 V, $V_{GS}$ = 0 V, f = 1 Mhz		331		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			213				

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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2

0.6

20

30

0.8

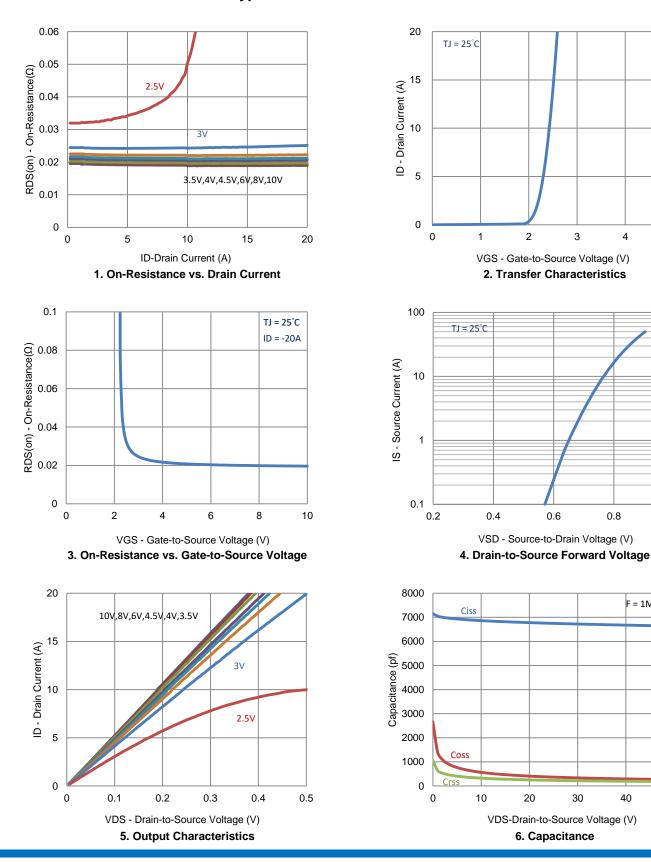
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1

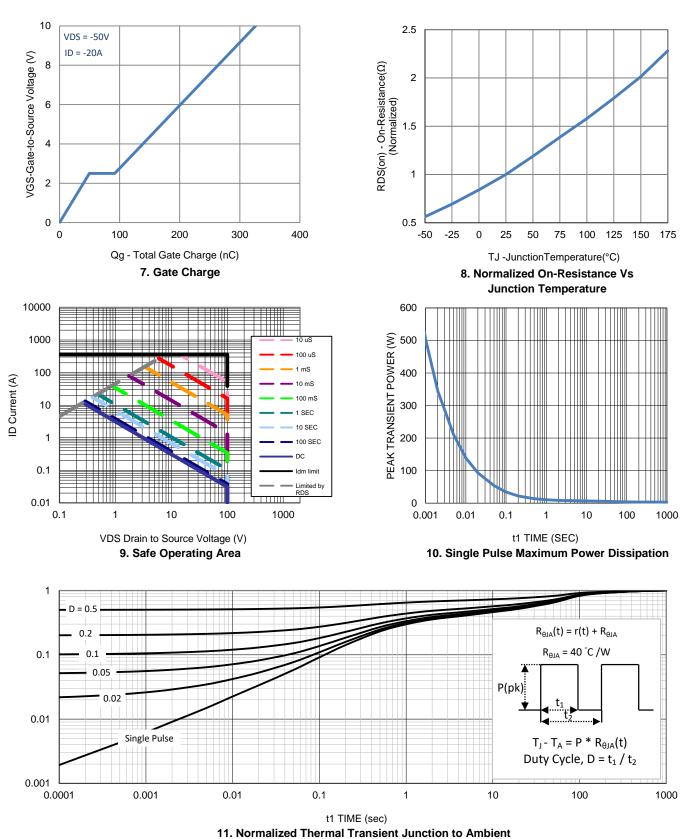
F = 1MHz



### **Typical Electrical Characteristics**

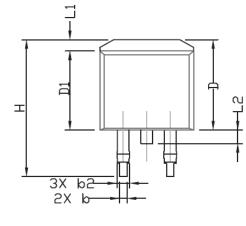
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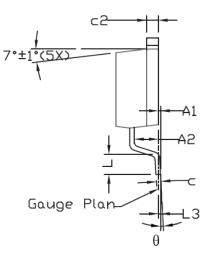
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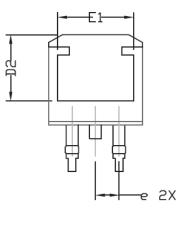


# **Typical Electrical Characteristics**

# **Package Information**







DIMENSIONAL REQM			REQMTS	INCHES REQMTS			
SYMBOL	MIN	NLM	MAX	MIN	NLM	MAX	
A	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2,57	2,67	0.097	0.101	0.105	
6	0.69	0.813	0.94	0.027	0.032	0.037	
b2	1,17	1,27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0.60	0.019	0.020	0.024	
c2	1,17	1.27	1.37	0.046	0.050	0.054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8,78	9,65	0.340	0.346	0,380	
D2	7.12	7.37	7,62	0.280	0,290	0.300	
E	9,70	10.15	10.54	0.382	0.400	0.415	
E1	8,00	8,20	8,40	0.315	0,323	0,331	
e	2.54 BSC			0.100 BSC			
H	14.99	15,24	15,49	0.590	0.600	0.610	
L	1.78	2.29	2,79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0.060	
L2			1,75			0.069	
L3		0,254			0.010		
θ	0*		8*	0*		8*	